













# 6-Pin DIP Optoisolators AC Input/Transistor Output

The H11AA1, H11AA2, H11AA3, H11AA4 devices consist of two gallium—arsenide infrared emitting diodes connected in inverse parallel, optically coupled to a monolithic silicon phototransistor detector.

- Built-In Protection for Reverse Polarity
- Guaranteed CTR Minimum Values as High as 100%
- · Guaranteed Minimum/Maximum Symmetry Limits
- To order devices that are tested and marked per VDE 0884 requirements, the suffix "V" must be included at end of part number. VDE 0884 is a test option.

#### **Applications**

· Detecting or Monitoring ac Signals

Detector Power Dissipation @ TA = 25°C

with Negligible Power in Input LEDs

- AC Line/Digital Logic Isolation
- Programmable Controllers
- · Interfacing and coupling systems of different potentials and impedances
- AC/DC Input Modules

#### **MAXIMUM RATINGS** (T<sub>A</sub> = 25°C unless otherwise noted)

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|--|--------|-------------|-------------|--|
| Rating   | Symbol | Value       | Unit        |  |
| INPUT LED  | -      |             |             |  |
| Forward Current — Continuous (RMS)   | lF     | 60          | mA          |  |
| LED Power Dissipation @ T <sub>A</sub> = 25°C with Negligible Power in Output Detector Derate above 25°C | PD     | 120<br>1.41 | mW<br>mW/°C |  |
| OUTPUT TRANSISTOR  |        | 1.41        | 1111117     |  |
| Collector–Emitter Voltage  | VCEO   | 30          | Volts       |  |
| Emitter–Base Voltage   | VEBO   | 5           | Volts       |  |
| Collector-Base Voltage   | VCBO   | 70          | Volts       |  |
| Collector Current — Continuous   | lс     | 150         | mA          |  |

 $P_D$ 

150

1.76

mW

mW/°C

#### TOTAL DEVICE

Derate above 25°C

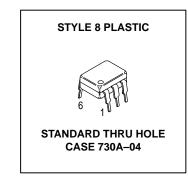
| Isolation Surge Voltage <sup>(1)</sup> (Peak ac Voltage, 60 Hz, 1 sec Duration) | VISO             | 7500        | Vac(pk)     |
|---|------------------|-------------|-------------|
| Total Device Power Dissipation @ T <sub>A</sub> = 25°C<br>Derate above 25°C     | P <sub>D</sub>   | 250<br>2.94 | mW<br>mW/°C |
| Ambient Operating Temperature Range(2)  | T <sub>A</sub>   | -55 to +100 | °C          |
| Storage Temperature Range(2)  | T <sub>stg</sub> | -55 to +150 | °C          |
| Soldering Temperature (10 sec, 1/16" from case)                                 | TL               | 260         | °C          |

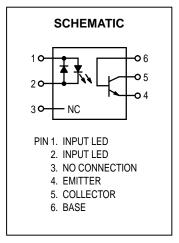
- 1. Isolation surge voltage is an internal device dielectric breakdown rating. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.
- 2. Refer to Quality and Reliability Section in Opto Data Book for information on test conditions.

**Preferred** devices are Motorola recommended choices for future use and best overall value. GlobalOptoisolator is a trademark of Motorola, Inc.

H11AA1\*
[CTR = 20% Min]
H11AA2
[CTR = 10% Min]
H11AA3
[CTR = 50% Min]
H11AA4\*
[CTR = 100% Min]

\*Motorola Preferred Devices







# H11AA1 H11AA2 H11AA3 H11AA4

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$  unless otherwise noted)(1)

| Characteristic   |                       |  | Symbol                              | Min                                    | <b>Typ</b> (1)                           | Max              | Unit           |
|--|-----------------------|--|-------------------------------------|--|--|------------------|----------------|
| NPUT LED   |                       |  |                                     | •                                      |  |                  | •              |
| Forward Voltage (IF = 10 mA, either direction) $ T_{A} = - $ $ T_{A} = 1 $     |                       | H11AA1,3,4<br>H11AA2<br>All devices<br>All devices | VF                                  | _<br>_<br>_<br>_                       | 1.15<br>1.15<br>1.3<br>1.05              | 1.5<br>1.8<br>—  | Volts          |
| Capacitance (V = 0 V, f = 1 MHz)   |                       |  | CJ                                  | _                                      | 20                                       | _                | pF             |
| OUTPUT TRANSISTOR  |                       |  | •                                   | 1                                      |  |                  |                |
| Collector–Emitter Dark Current (V <sub>CE</sub> = 10 V) T <sub>A</sub> = 1     | 00°C                  | H11AA1,3,4<br>H11AA2<br>All devices                | ICEO                                | _<br>_<br>_                            | 1<br>1<br>1                              | 100<br>200<br>—  | nA<br>nA<br>μA |
| Collector-Base Dark Current (V <sub>CB</sub> = 10 V)                           |                       |  | ІСВО                                | _                                      | 0.2                                      | _                | nA             |
| Collector-Emitter Breakdown Voltage (I <sub>C</sub> =                          | 10 mA)                |  | V(BR)CEO                            | 30                                     | 45                                       | _                | Volts          |
| Collector–Base Breakdown Voltage (I <sub>C</sub> = 100 μA)                     |                       |  | V(BR)CBO                            | 70                                     | 100                                      | _                | Volts          |
| Emitter–Collector Breakdown Voltage (I <sub>E</sub> = 100 μA)                  |                       |  | V <sub>(BR)ECO</sub>                | 5                                      | 7.8                                      | _                | Volts          |
| DC Current Gain (I <sub>C</sub> = 2 mA, V <sub>CE</sub> = 5 V) (Typical Value) |                       | hFE  | _                                   | 500                                    | _  | _                |                |
| Collector–Emitter Capacitance (f = 1 MHz, V <sub>CE</sub> = 0 V)               |                       | C <sub>CE</sub>                                    | _                                   | 1.7                                    | _  | pF               |                |
| Collector-Base Capacitance (f = 1 MHz, V <sub>CB</sub> = 0 V)                  |                       | ССВ  | _                                   | 20                                     | _  | pF               |                |
| Emitter–Base Capacitance (f = 1 MHz, V <sub>EB</sub> = 0 V)                    |                       | C <sub>EB</sub>                                    | _                                   | 10                                     | _  | pF               |                |
| COUPLED  |                       |  | •                                   | •                                      |  |                  | •              |
| Output Collector Current (IF = $\pm$ 10 mA, VCE = 10 V)                        |                       | H11AA1<br>H11AA2<br>H11AA3<br>H11AA4               | I <sub>C</sub> (CTR) <sup>(2)</sup> | 2 (20)<br>1 (10)<br>5 (50)<br>10 (100) | 5 (50)<br>2 (20)<br>10 (100)<br>15 (150) | _<br>_<br>_<br>_ | mA (%)         |
| Output Collector Current Symmetry(3)   | CE = 10               | H11AA1,3,4   | _                                   | 0.33                                   | _  | 3                | _              |
| Collector-Emitter Saturation Voltage (I <sub>C</sub> = 0                       | .5 mA, I <sub>F</sub> | = ± 10 mA)   | VCE(sat)                            | _                                      | 0.1                                      | 0.4              | Volts          |
| Isolation Voltage (f = 60 Hz, t = 1 sec) <sup>(4)</sup>                        |                       | VISO   | 7500                                | _                                      | _  | Vac(pk           |                |
| Isolation Resistance (V = 500 V) <sup>(4)</sup>                                |                       |  | RISO                                | 10 <sup>11</sup>                       | _  | _                | Ω              |
| Isolation Capacitance (V = 0 V, f = 1 MHz)(4                                   | .)                    |  | C <sub>ISO</sub>                    | _                                      | 0.2                                      | _                | pF             |

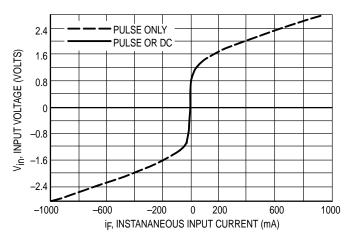
<sup>1.</sup> Always design to the specified minimum/maximum electrical limits (where applicable).

<sup>2.</sup> Current Transfer Ratio (CTR) =  $I_C/I_F \times 100\%$ .

<sup>3.</sup> This specification guarantees that the higher of the two  $I_C$  readings will be no more than 3 times the lower at  $I_F = 10$  mA.

<sup>4.</sup> For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

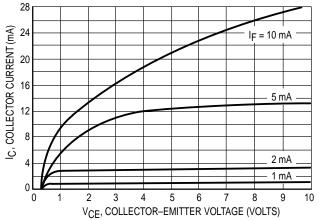
#### **TYPICAL CHARACTERISTICS**

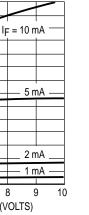


INPUT CURRENT WAVEFORM MAXIMUM PEAK OUTPUT CURRENT (1) MINIMUM PEAK OUTPUT CURRENT (1)

Figure 1. Input Voltage versus Input Current

Figure 2. Output Characteristics





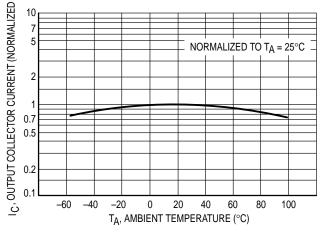
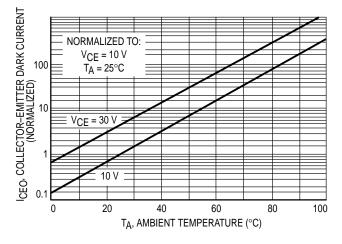


Figure 3. Collector Current versus Collector-Emitter Voltage

Figure 4. Output Current versus Ambient Temperature



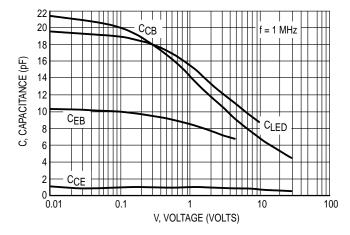
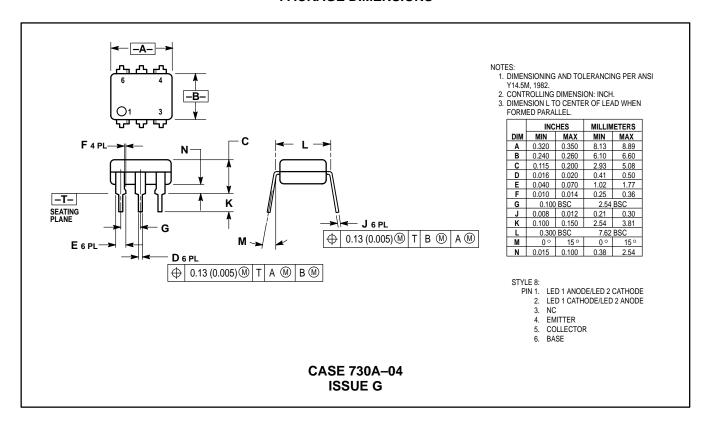


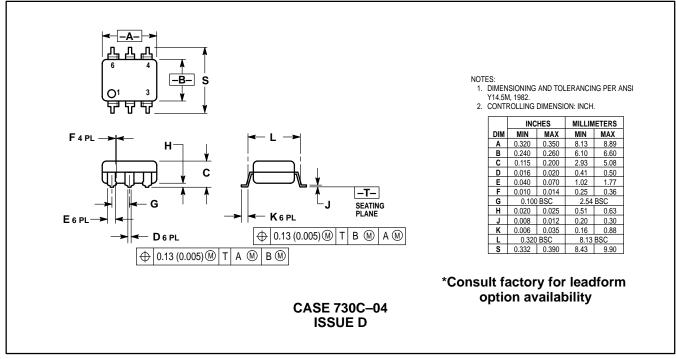
Figure 5. Dark Current versus Ambient Temperature

Figure 6. Capacitances versus Voltage

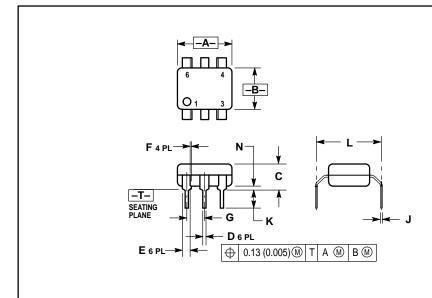
#### Η11ΔΔ1 Η11ΔΔ2 Η11ΔΔ3 Η11ΔΔ4

#### PACKAGE DIMENSIONS





# H11AA1 H11AA2 H11AA3 H11AA4



**CASE 730D-05 ISSUE D** 

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

|     | INCHES    |       | MILLIN | IETERS   |  |
|-----|-----------|-------|--------|----------|--|
| DIM | MIN       | MAX   | MIN    | MAX      |  |
| Α   | 0.320     | 0.350 | 8.13   | 8.89     |  |
| В   | 0.240     | 0.260 | 6.10   | 6.60     |  |
| С   | 0.115     | 0.200 | 2.93   | 5.08     |  |
| D   | 0.016     | 0.020 | 0.41   | 0.50     |  |
| Е   | 0.040     | 0.070 | 1.02   | 1.77     |  |
| F   | 0.010     | 0.014 | 0.25   | 0.36     |  |
| G   | 0.100 BSC |       | 2.54   | 2.54 BSC |  |
| J   | 0.008     | 0.012 | 0.21   | 0.30     |  |
| K   | 0.100     | 0.150 | 2.54   | 3.81     |  |
| L   | 0.400     | 0.425 | 10.16  | 10.80    |  |
| N   | 0.015     | 0.040 | 0.38   | 1.02     |  |

\*Consult factory for leadform option availability

### H11AA1 H11AA2 H11AA3 H11AA4

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